

ECEN689: Special Topics in High-Speed Links Circuits and Systems Spring 2010

Lecture 33: Optical I/O



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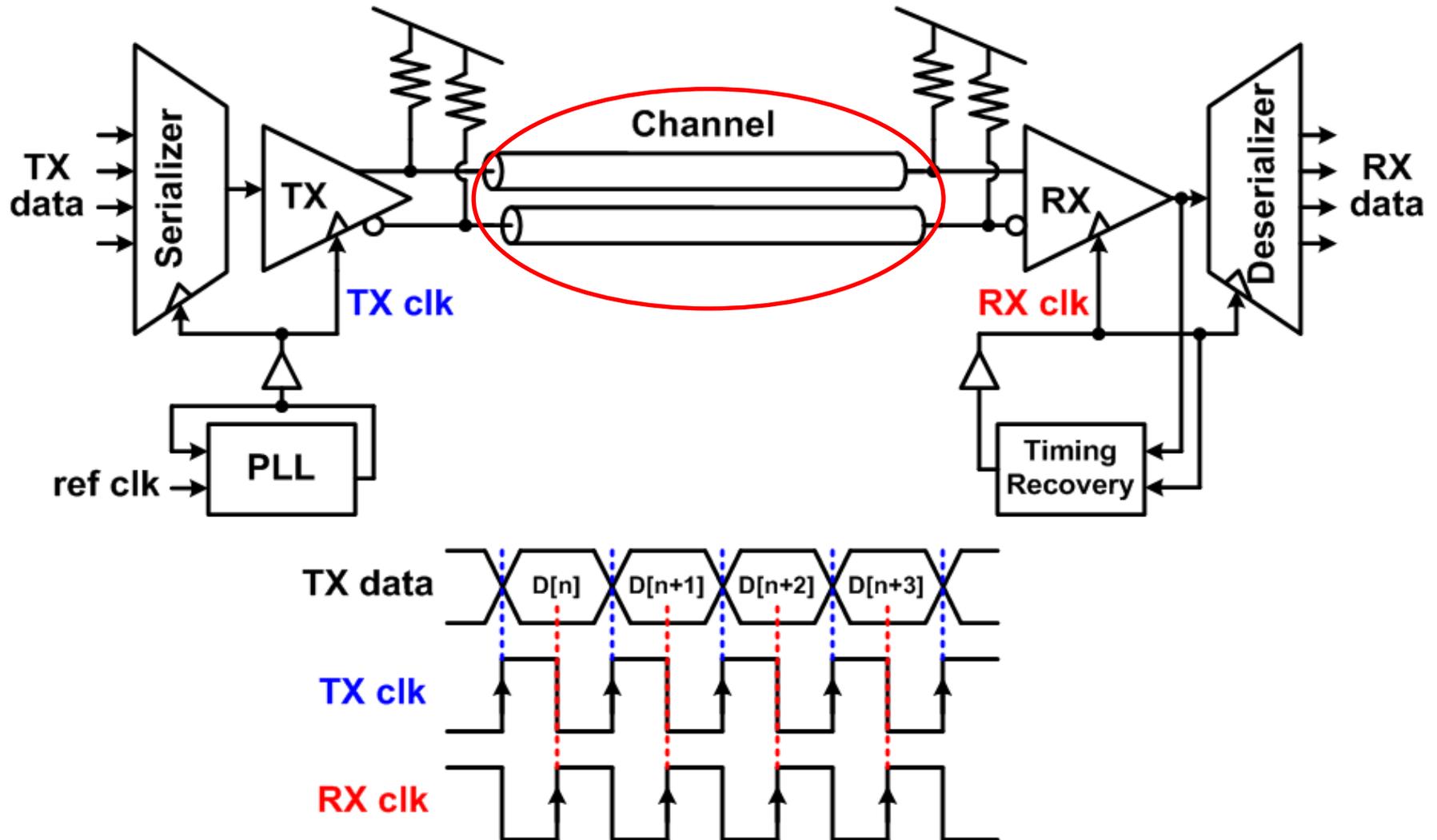
Announcements

- Final Project Report Due Tomorrow by 5PM
- Project Presentations next Monday May 10, 8-10AM

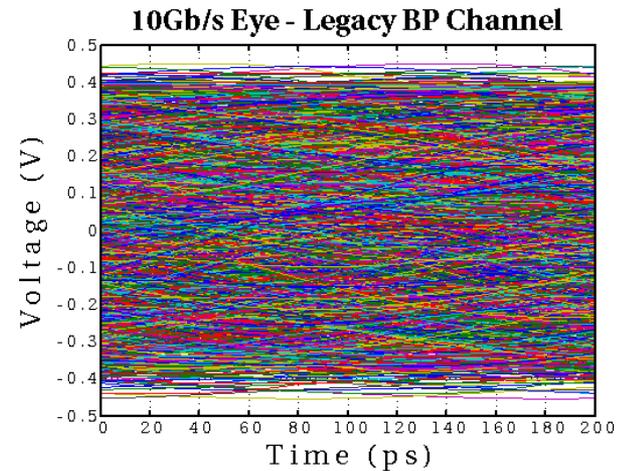
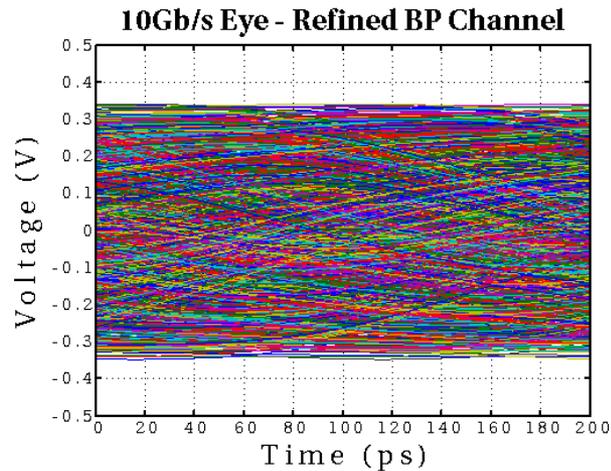
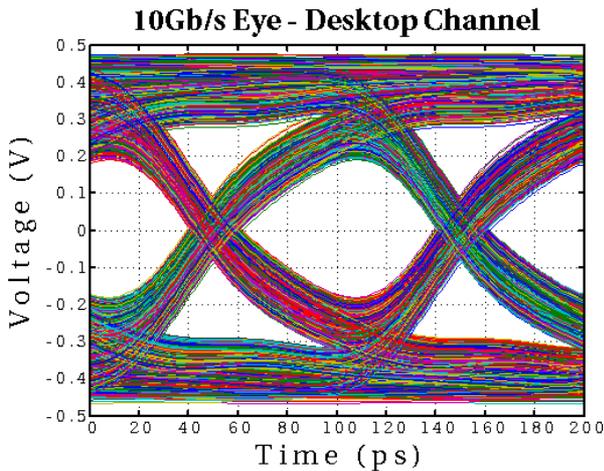
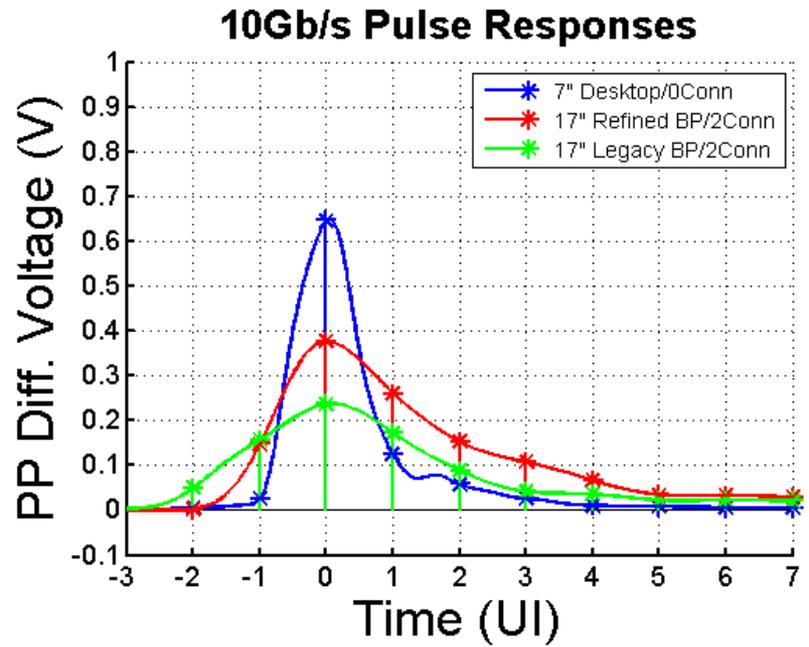
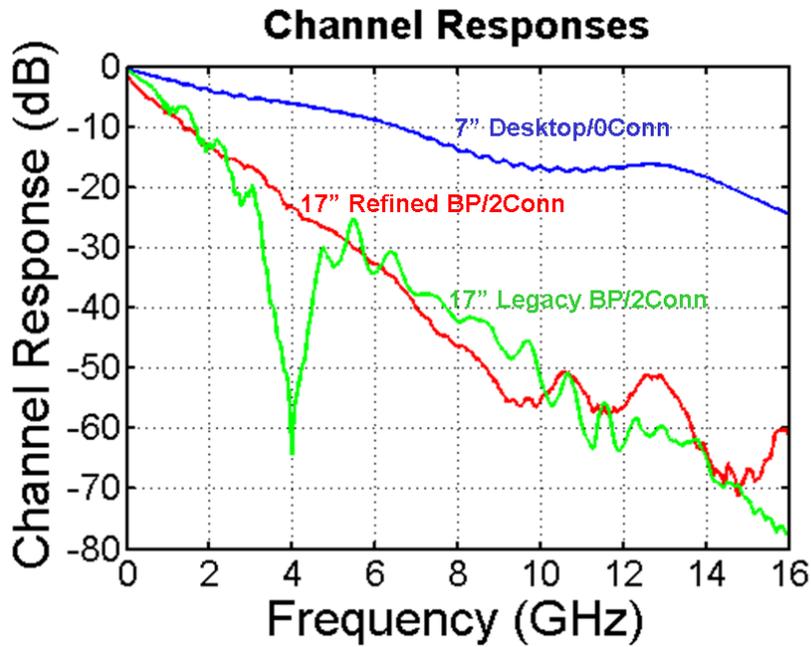
Agenda

- Electrical Channel Issues
- Optical Channel
- Optical Transmitter Technology
- Optical Receiver Technology
- Optical Integration Approaches

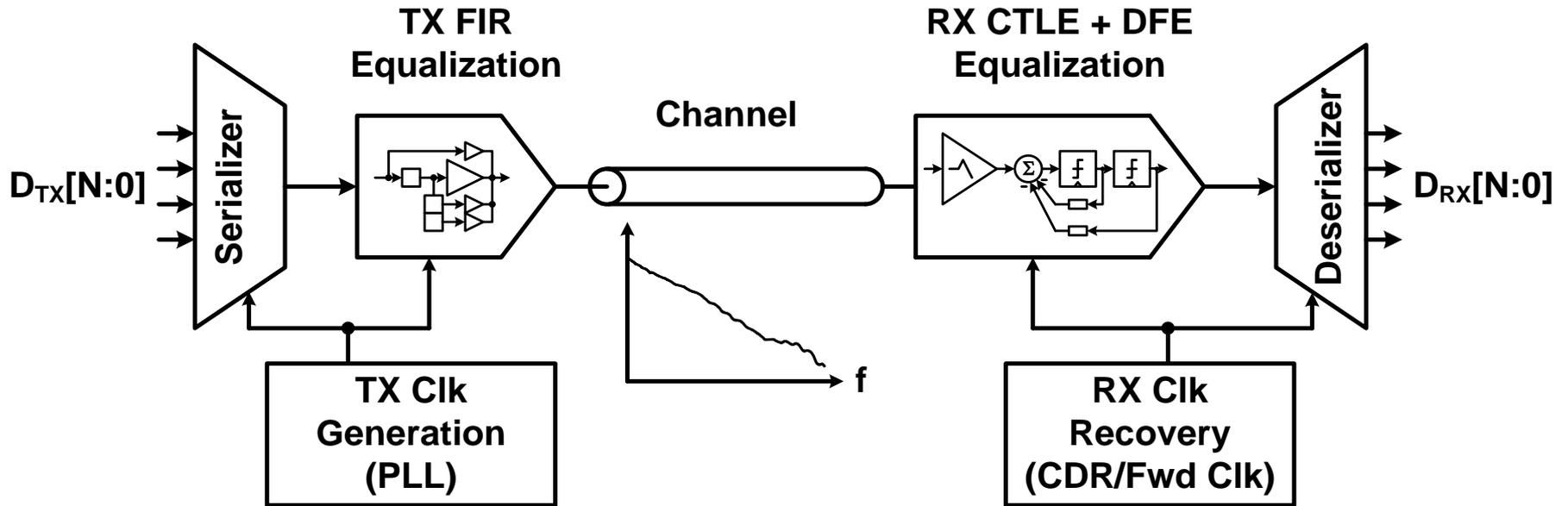
High-Speed Electrical Link System



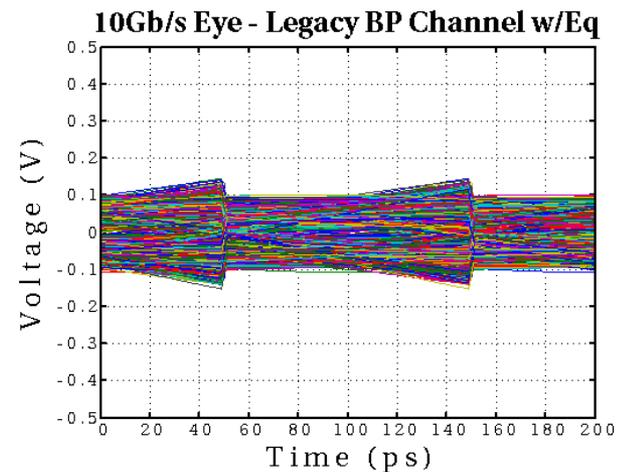
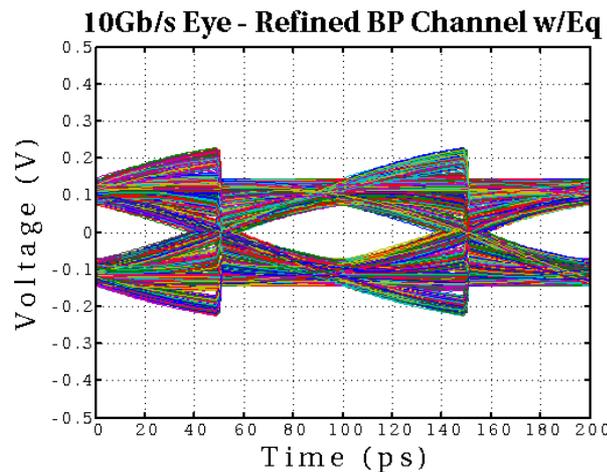
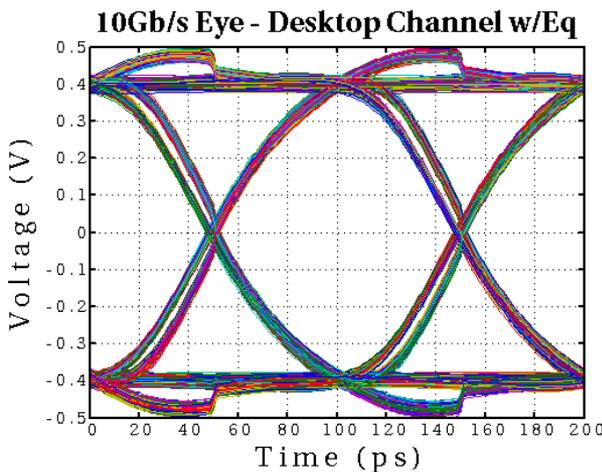
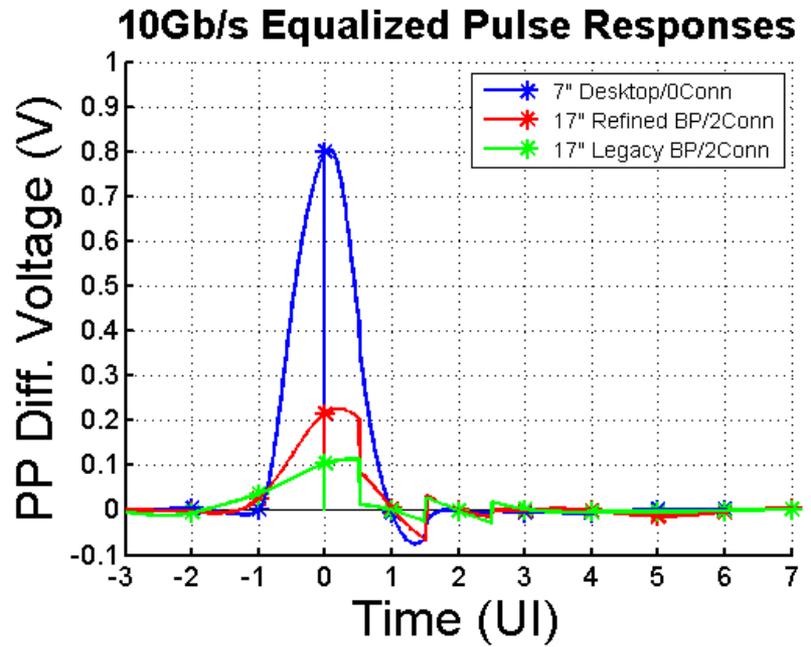
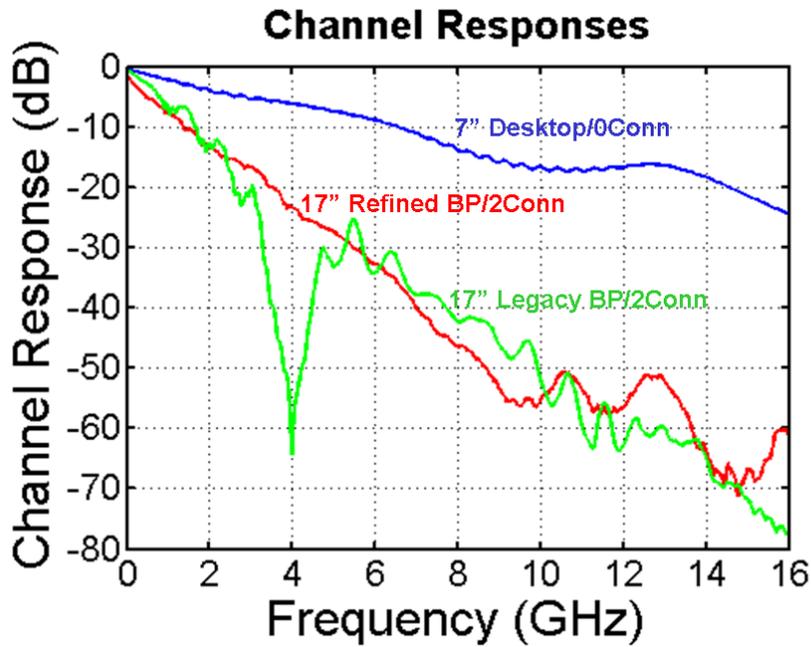
Channel Performance Impact



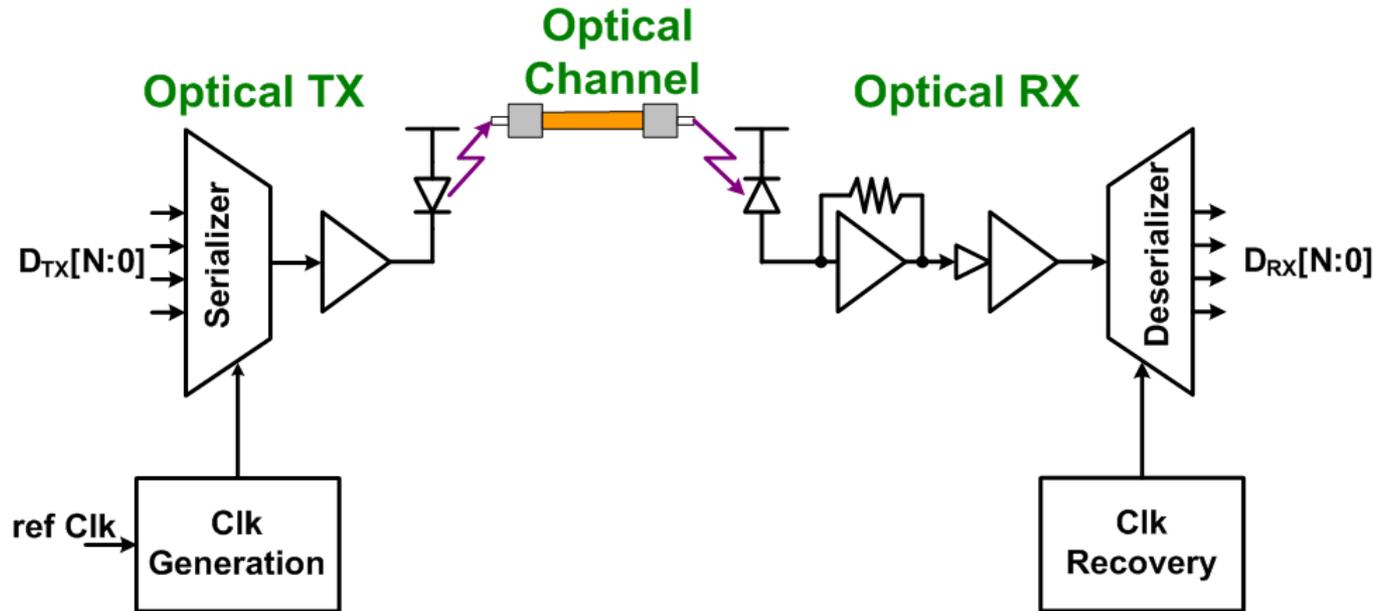
Link with Equalization



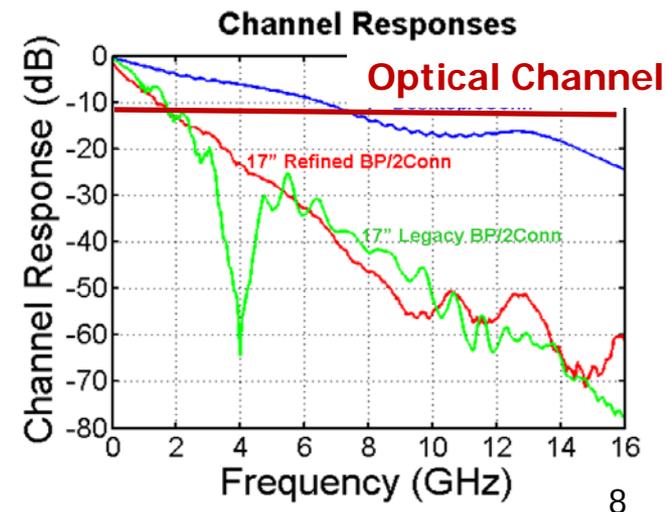
Channel Performance Impact



High-Speed Optical Link System



- Optical interconnects remove many channel limitations
 - Reduced complexity and power consumption
 - Potential for high information density with wavelength-division multiplexing (WDM)



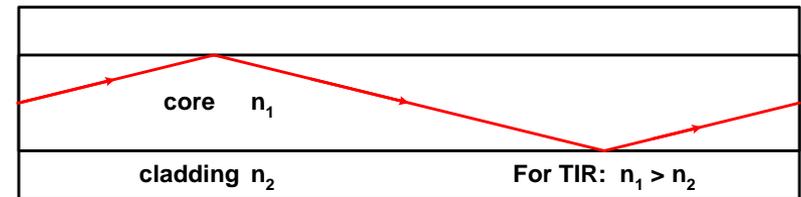
Optical Channels

- Short distance optical I/O channels are typically either waveguide (fiber)-based or free-space
- Optical channel advantages
 - Much lower loss
 - Lower cross-talk
 - Smaller waveguides relative to electrical traces
 - Potential for multiple data channels on single fiber via WDM

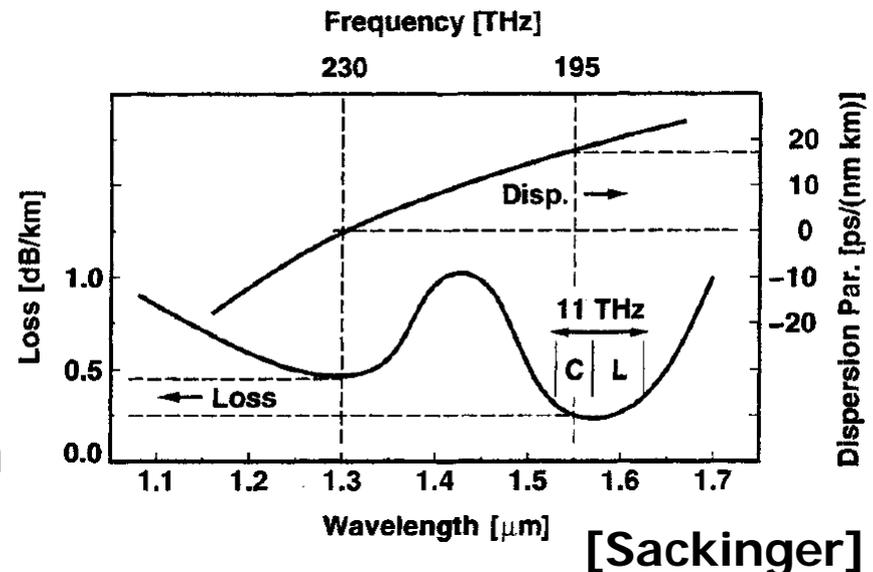
Waveguide (Fiber)-Based Optical Links

- Optical fiber loss is specified in dB/km
 - Single-Mode Fiber loss ~0.25dB/km at 1550nm
 - RF coaxial cable loss ~100dB/km at 10GHz
- Frequency dependent loss is very small
 - <0.5dB/km over a bandwidth >10THz
- Bandwidth may be limited by dispersion (pulse-spreading)
 - Important to limit laser linewidth for long distances (>1km)

Optical Fiber Cross-Section

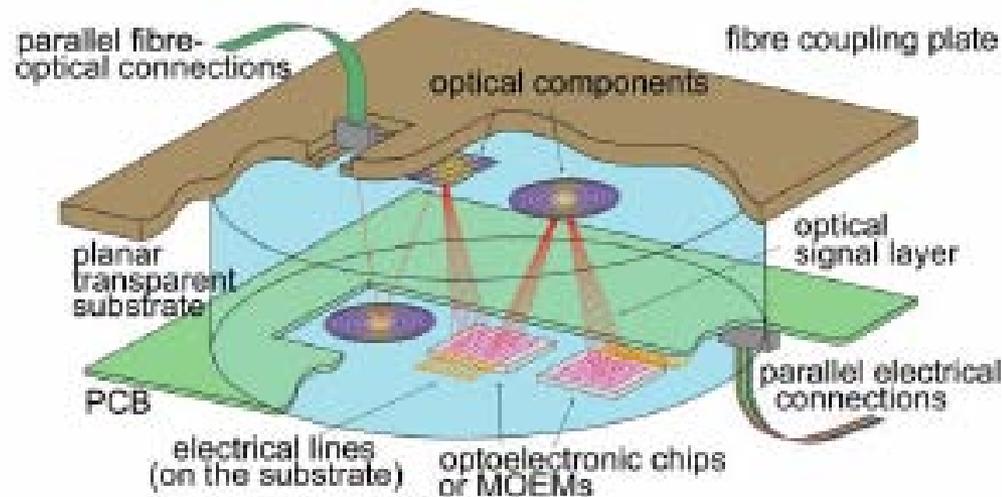


Single-Mode Fiber Loss & Dispersion



Free-Space Optical Links

[Gruber]



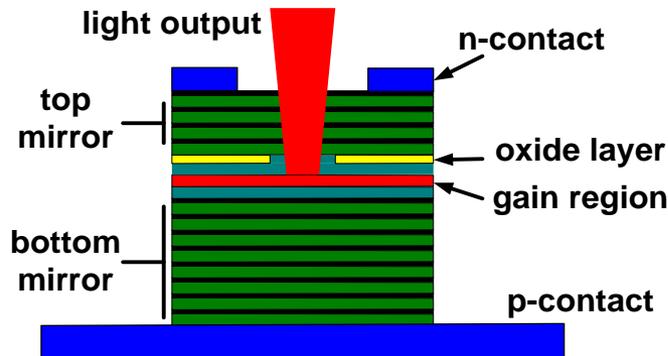
- Free-space (air or glass) interconnect systems have also been proposed
- Optical imaging system routes light chip-to-chip

Optical Transmitter Technology

- Optical modulation techniques
 - Direct modulation of laser
 - External modulation of continuous-wave (CW) “DC” laser with absorptive or refractive modulators
- Optical sources for chip-to-chip links
 - Vertical-Cavity Surface-Emitting Laser (VCSEL)
 - Electro-Absorption Modulator (EAM)
 - Ring-Resonator Modulator (RRM)
 - Mach-Zehnder Modulator (MZM)

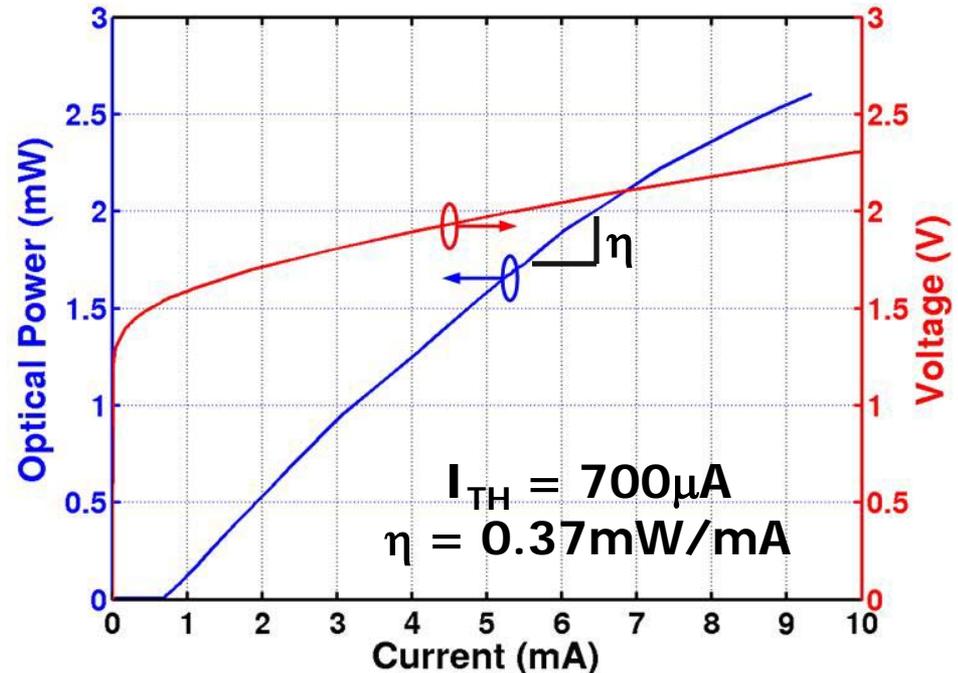
Vertical-Cavity Surface-Emitting Laser (VCSEL)

VCSEL Cross-Section



- VCSEL emits light perpendicular from top (or bottom) surface
- Important to always operate VCSEL above threshold current, I_{TH} , to prevent “turn-on delay” which results in ISI
- Operate at finite extinction ratio (P_1/P_0)

VCSEL L-I-V Curves

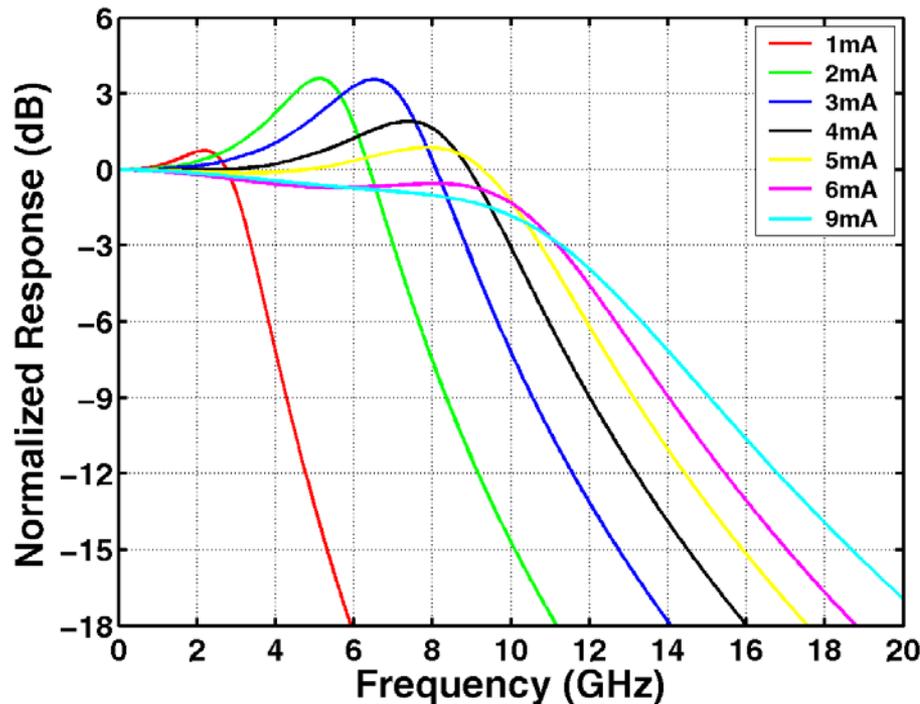


$$P_o = \eta(I - I_{TH})$$

$$\text{Slope Efficiency } \eta = \frac{\Delta P}{\Delta I} \left(\frac{\text{W}}{\text{A}} \right)$$

VCSEL Bandwidth vs Reliability

10Gb/s VCSEL Frequency Response [1]



$$BW \propto \sqrt{I_{avg} - I_{TH}}$$

- Mean Time to Failure (MTTF) is inversely proportional to current density squared

$$MTTF = \frac{A}{j^2} e^{\left(\frac{E_A}{k}\right)\left(\frac{1}{T_j} - \frac{1}{373}\right)} \quad [2]$$

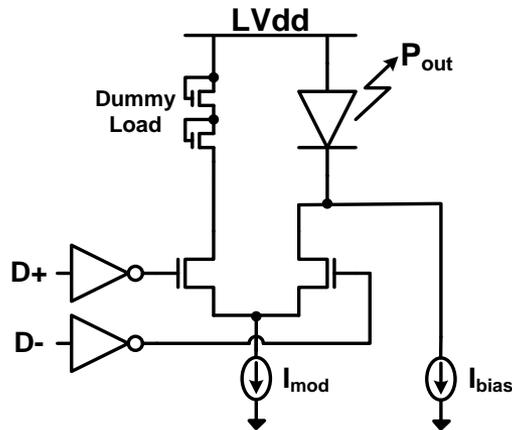
- Steep trade-off between bandwidth and reliability

$$MTTF \propto \frac{1}{BW^4}$$

1. D. Bossert *et al*, "Production of high-speed oxide confined VCSEL arrays for datacom applications," *Proceedings of SPIE*, 2002.
2. M. Teitelbaum and K. Goossen, "Reliability of Direct Mesa Flip-Chip Bonded VCSEL's," *LEOS*, 2004.

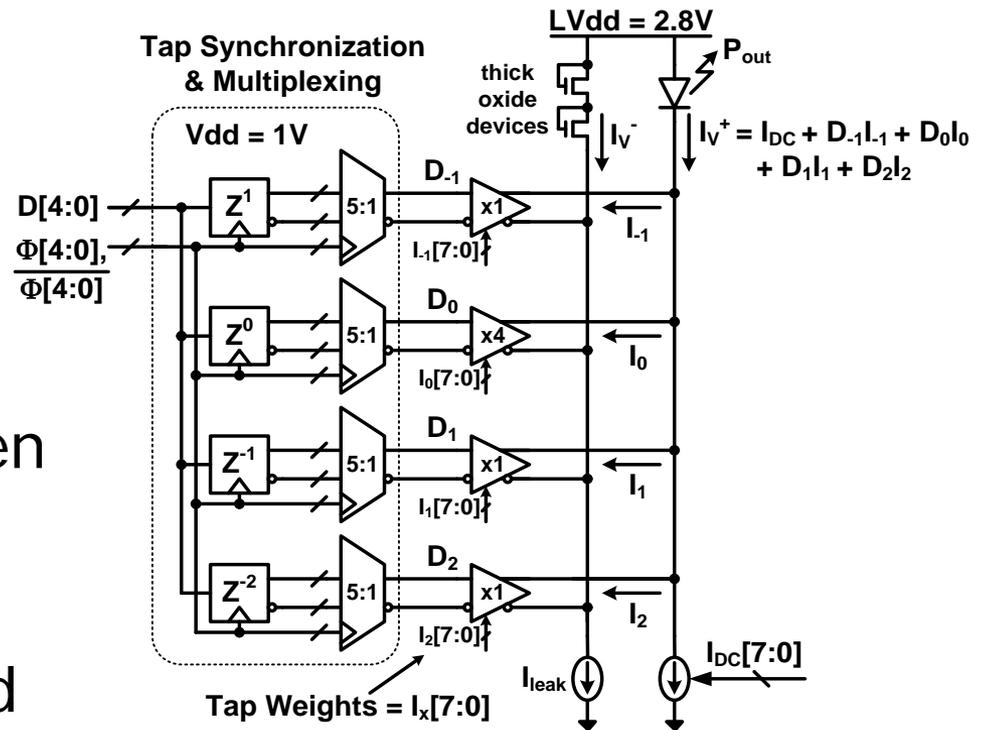
VCSEL Drivers

Current-Mode VCSEL Driver



- Current-mode drivers often used due to linear L-I relationship
- Equalization can be added to extend VCSEL bandwidth for a given current density

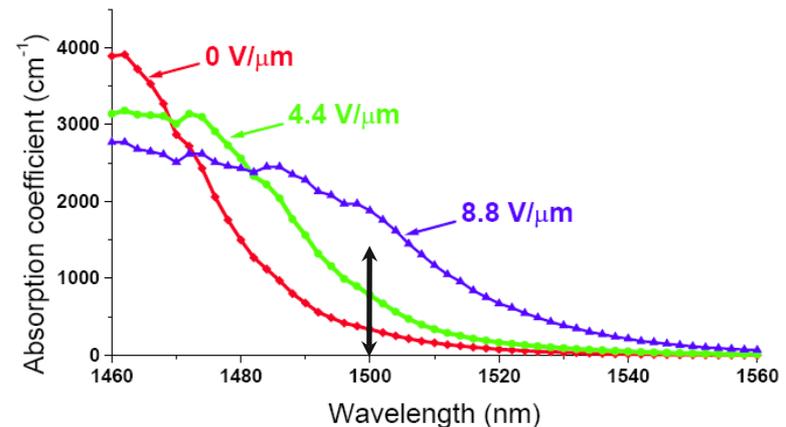
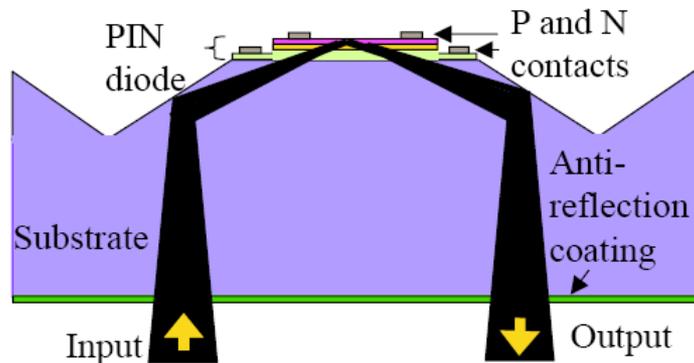
VCSEL Driver w/ 4-tap FIR Equalization



S. Palermo and M. Horowitz, "High-Speed Transmitters in 90nm CMOS for High-Density Optical Interconnects," *ESSCIRC*, 2006.

Electro-Absorption Modulator (EAM)

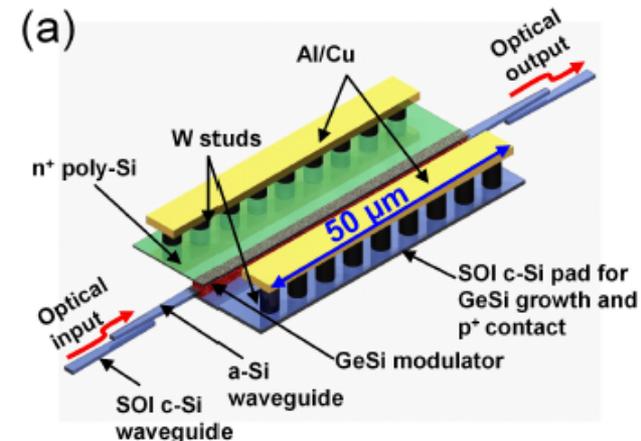
QWAFEM Modulator*



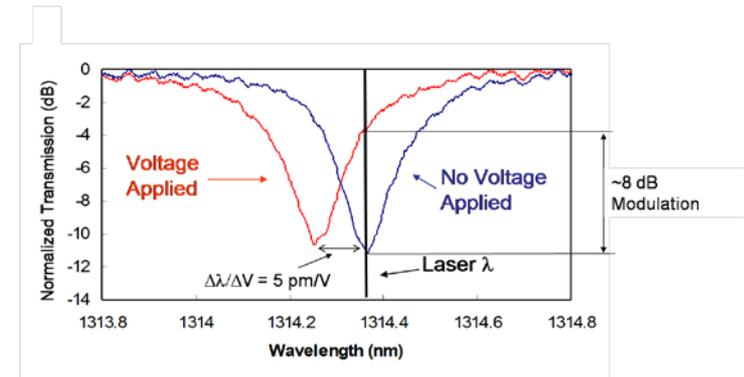
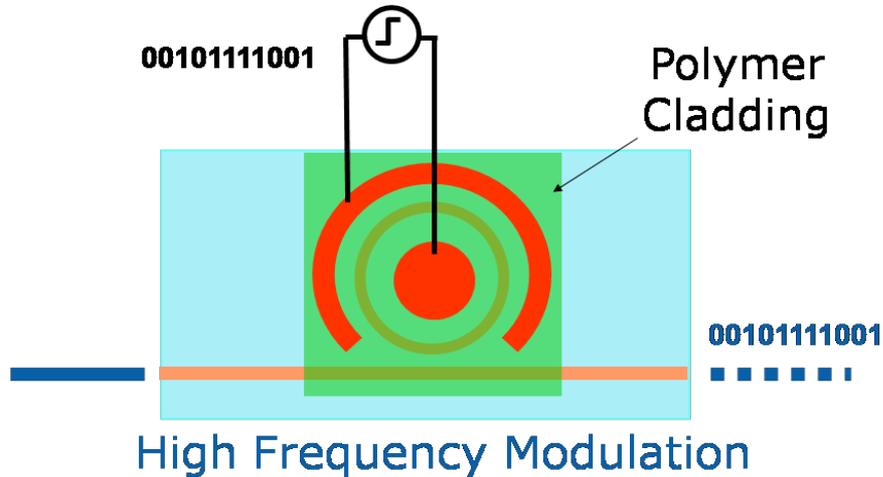
*N. Helman *et al*, "Misalignment-Tolerant Surface-Normal Low-Voltage Modulator for Optical Interconnects," *JSTQE*, 2005.

- Absorption edge shifts with changing bias voltage due to the "quantum-confined Stark or Franz-Keldysh effect" & modulation occurs
- Modulators can be surface-normal devices or waveguide-based
- Maximizing voltage swing allows for good contrast ratio over a wide wavelength range
- Devices are relatively small and can be treated as lump-capacitance loads
 - 10 – 500fF depending on device type

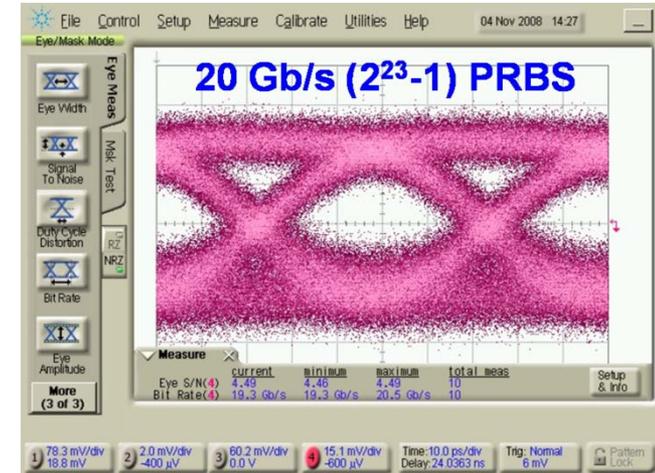
Waveguide EAM [Liu]



Ring-Resonator Modulator (RRM)

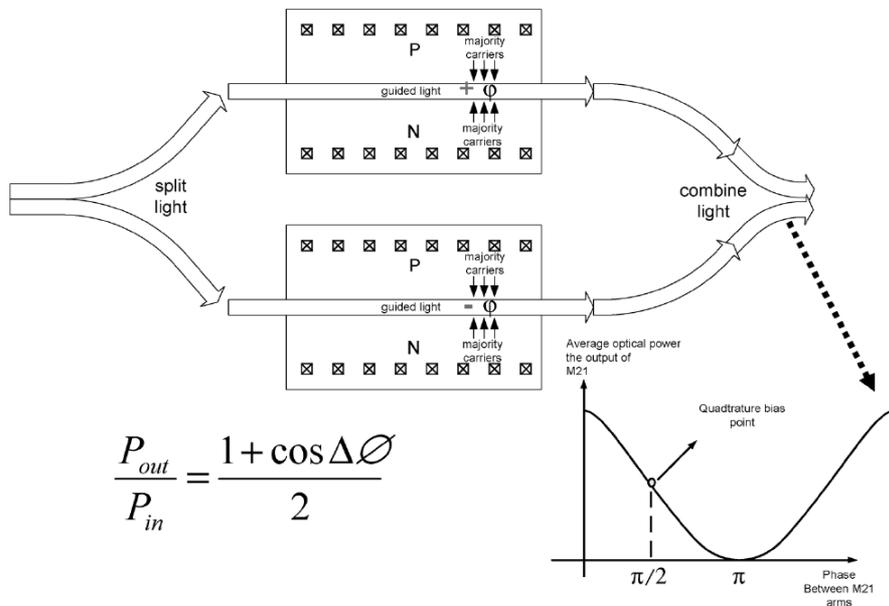


- Refractive devices which modulate by changing the interference light coupled into the ring with the waveguide light
- Devices are relatively small (ring diameters $< 20\mu\text{m}$) and can be treated as lumped capacitance loads ($\sim 10\text{fF}$)
- Devices can be used in WDM systems to selectively modulate an individual wavelength or as a “drop” filter at receivers

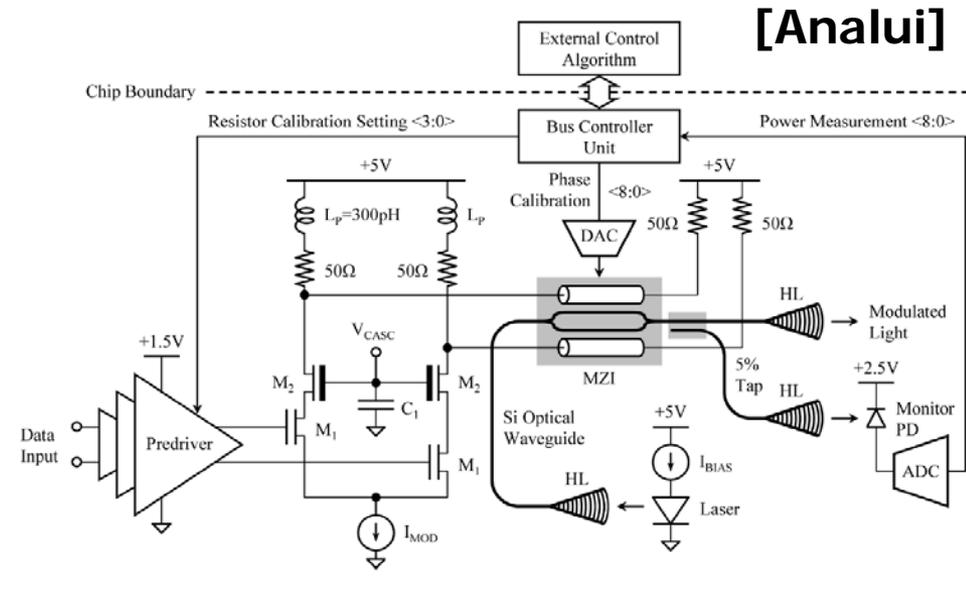


Optical Device Performance from: I. Young, E. Mohammed, J. Liao, A. Kern, **S. Palermo**, B. Block, M. Reshotko, and P. Chang, “Optical I/O Technology for Tera-Scale Computing,” *ISSCC*, 2009.

Mach-Zehnder Modulator (MZM)



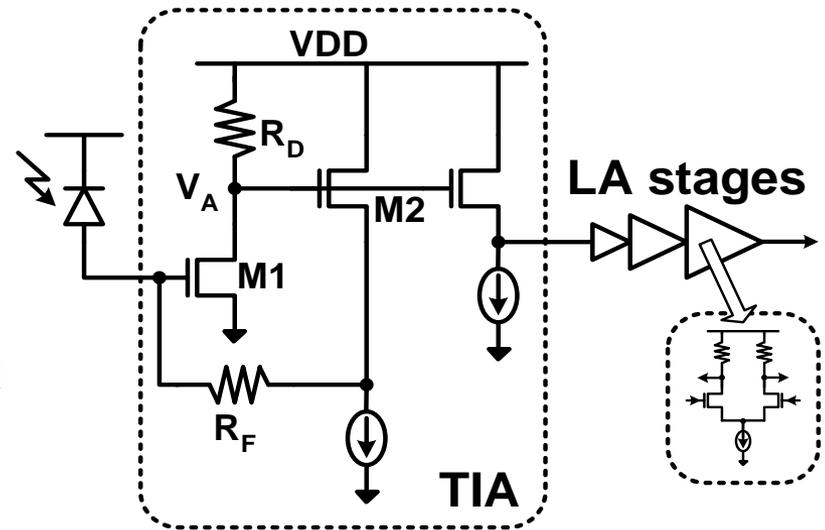
$$\frac{P_{out}}{P_{in}} = \frac{1 + \cos \Delta\phi}{2}$$



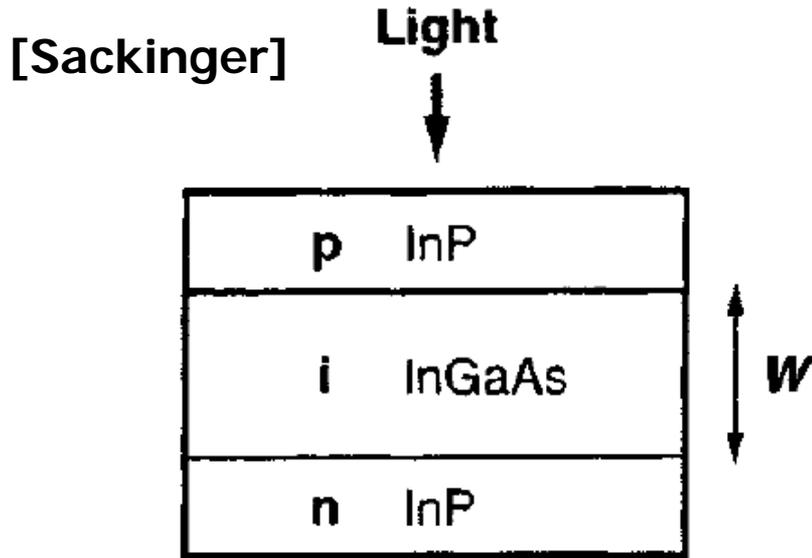
- Refractive modulator which splits incoming light into two paths, induces a voltage-controlled phase shift in the two paths, and recombines the light in or out of phase
- Long device (several mm) requires driver to drive low-impedance transmission line at potentially high swing ($5V_{ppd}$)
- While much higher power relative to RRM, they are less sensitive to temperature variations

Optical Receiver Technology

- Photodetectors convert optical power into current
 - p-i-n photodiodes
 - Integrated metal-semiconductor-metal photodetector
- Electrical amplifiers then convert the photocurrent into a voltage signal
 - Transimpedance amplifiers
 - Limiting amplifiers
 - Integrating optical receiver



p-i-n Photodiode



Responsivity:

$$\rho = \frac{I}{P_{opt}} = \frac{\eta_{pd} \lambda q}{hc} = 8 \times 10^5 (\eta_{pd} \lambda) \quad (\text{mA/mW})$$

Quantum Efficiency: $\eta_{pd} = 1 - e^{-\alpha W}$

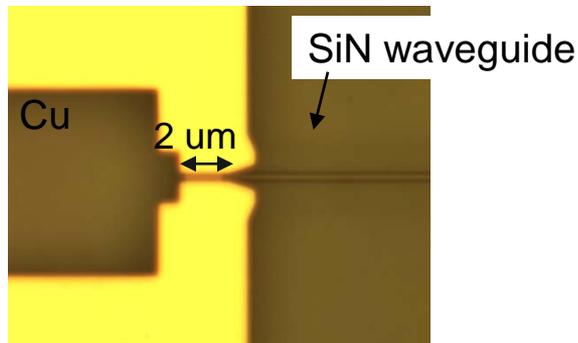
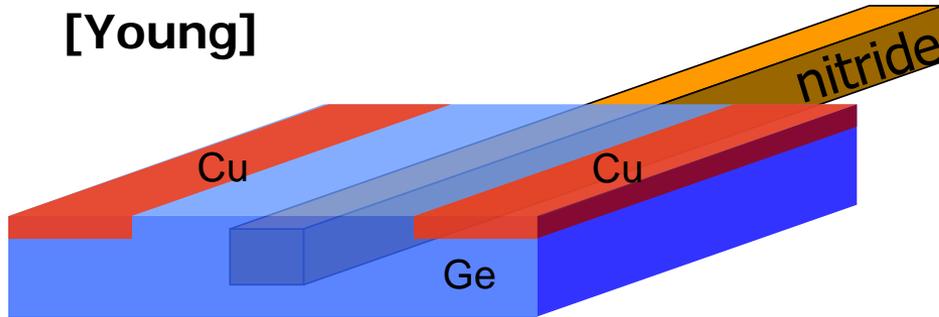
Transit-Time Limited Bandwidth:

$$f_{3dBPD} = \frac{2.4}{2\pi\tau_{tr}} = \frac{0.45v_{sat}}{W}$$

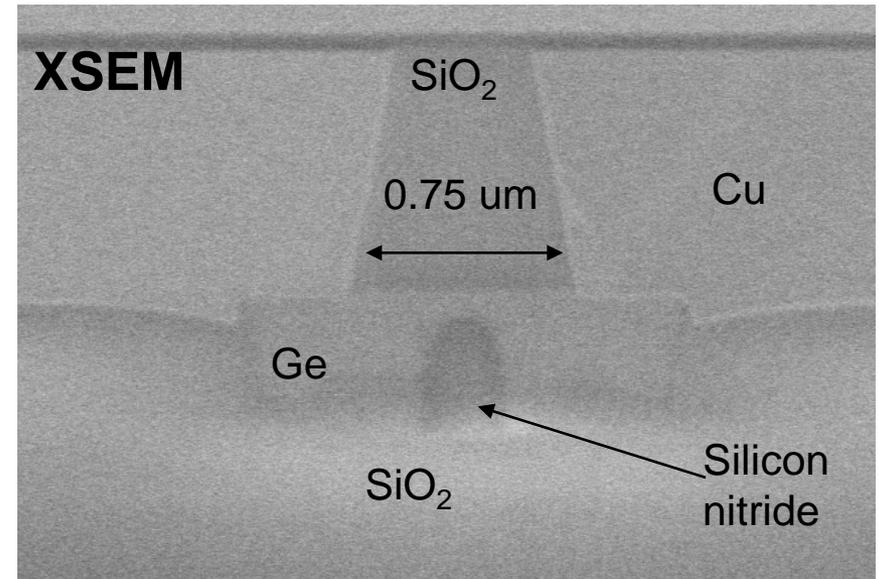
- Normally incident light absorbed in intrinsic region and generates carriers
- Trade-off between capacitance and transit-time
- Typical capacitance between 100-300fF

Integrated Ge MSM Photodetector

[Young]



Detector



Very low capacitance: <1 fF

Active area: < 2 μm²

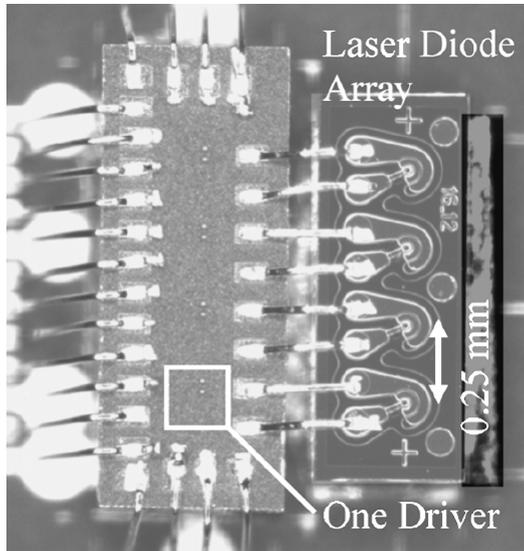
- Lateral Metal-Semiconductor-Metal (MSM Detector)
- Silicon Nitride Waveguide-Coupled
- Direct Germanium deposition on oxide

Optical Integration Approaches

- Efficient cost-effective optical integration approaches are necessary for optical interconnects to realize their potential for improved power efficiency at higher data rates
- Hybrid integration
 - Optical devices fabricated on a separate substrate
- Integrated CMOS photonics
 - Optical devices part of CMOS chip

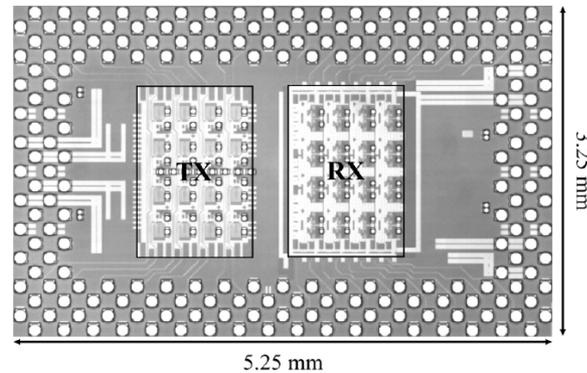
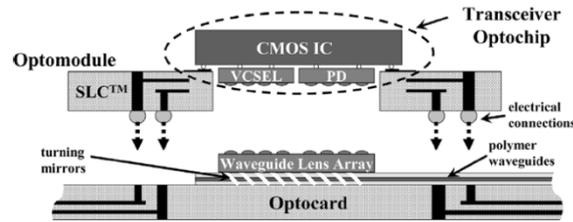
Hybrid Integration

[Kromer]



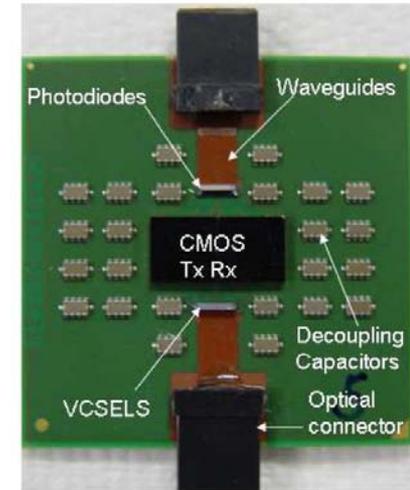
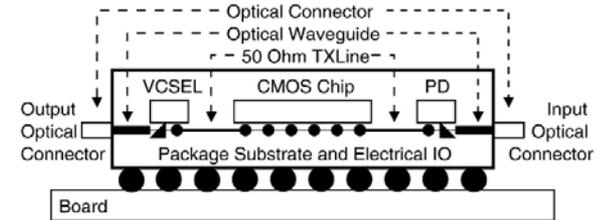
Wirebonding

[Schow]



Flip-Chip Bonding

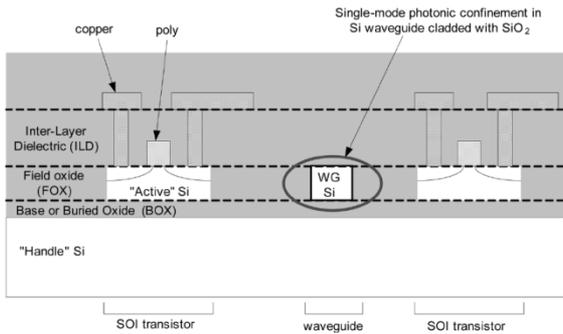
[Mohammed]



Short In-Package Traces

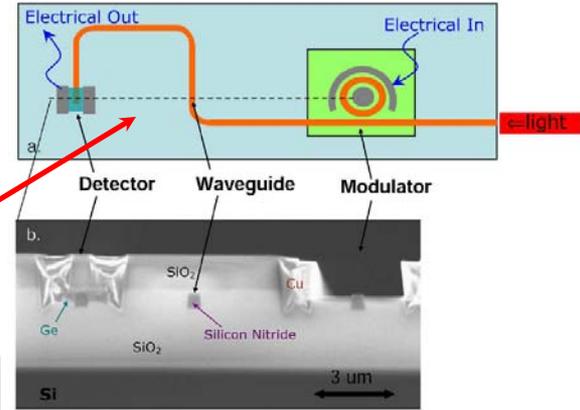
Integrated CMOS Photonics

SOI CMOS Process [Analui]



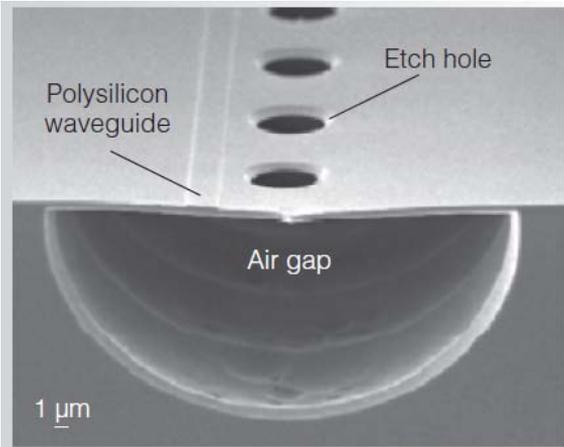
"Optics On Top"

Optical Layer

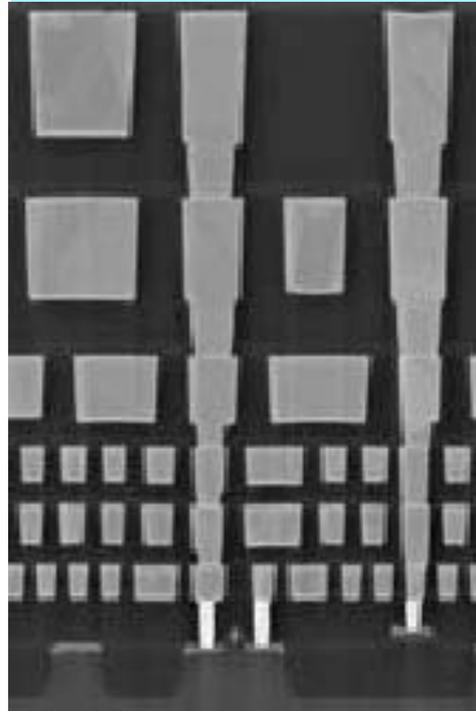


[Young]

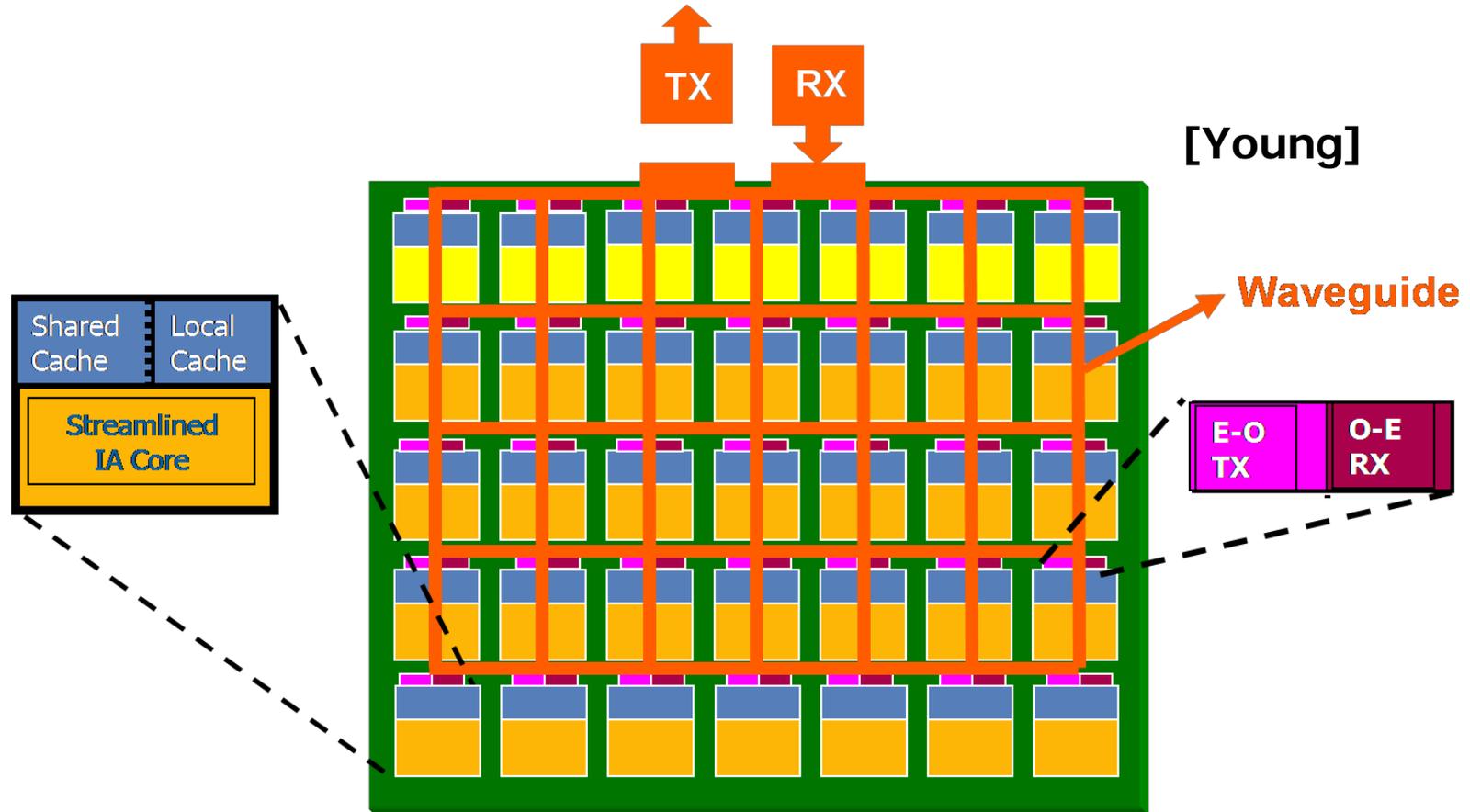
Bulk CMOS Process



[Batten]



Future Photonic CMOS Chip



- Unified optical interconnect for on-chip core-to-core and off-chip processor-to-processor and processor-to-memory

Conclusion

- Thanks for the fun semester!